HEF4511B

BCD to 7-segment latch/decoder/driver Rev. 7 — 11 November 2011

Product data sheet

General description 1.

The HEF4511B is a BCD to 7-segment latch/decoder/driver with four address inputs (D0 to D3), an active HIGH latch enable input (LE), an active LOW ripple blanking input (BL), an active LOW lamp test input (LT), and seven active HIGH NPN bipolar transistor segment outputs (Qa to Qg).

When LE is LOW and BL is HIGH, the state of the segment outputs (Qa to Qg) is determined by the data on D0 to D3. When LE goes HIGH, the last data present on D0 to D3 is stored in the latches and the segment outputs remain unchanged. When LT is LOW, all of the segment outputs are HIGH independent of all other input conditions. With LT HIGH, a LOW on BL forces all segment outputs LOW. The inputs \overline{LT} and \overline{BL} do not affect the latch circuit.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD}, V_{SS}, or another input.

Features and benefits 2.

- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Specified from -40 °C to +85 °C and -40 °C to +125 °C
- Complies with JEDEC standard JESD 13-B

3. Ordering information

Table 1. **Ordering information**

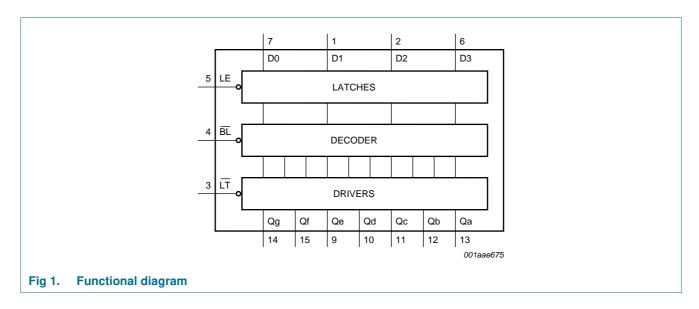
All types operate from -40 °C to +125 °C.

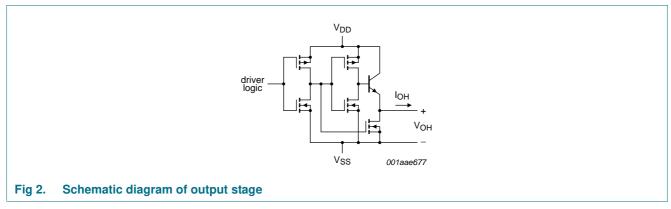
Type number	Package		
	Name	Description	Version
HEF4511BP	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
HEF4511BT	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1



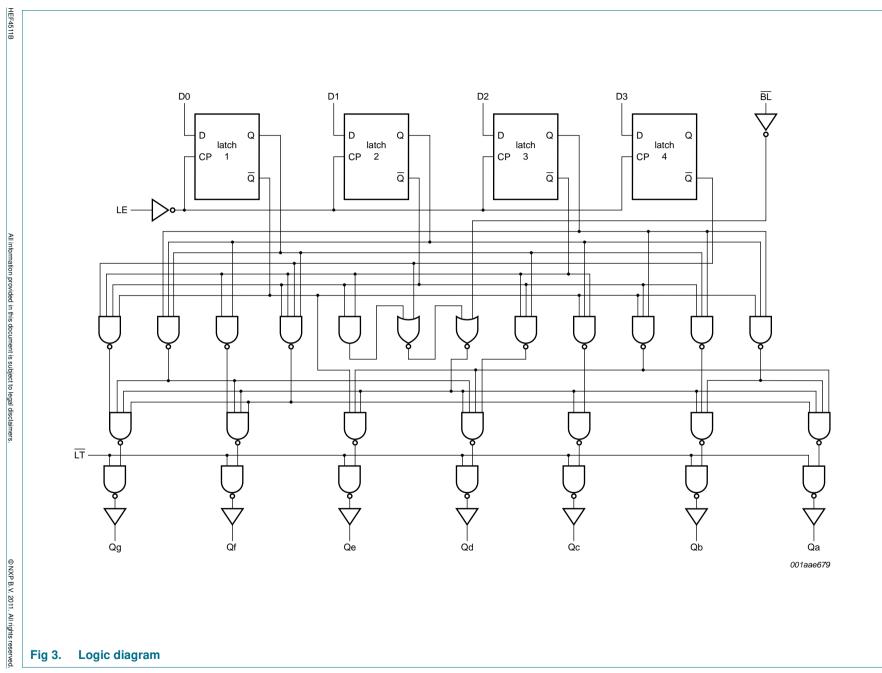
BCD to 7-segment latch/decoder/driver

4. Functional diagram





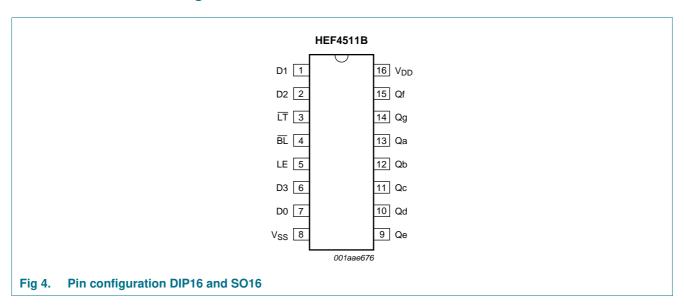




BCD to 7-segment latch/decoder/driver

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
ĪŢ	3	lamp test input (active LOW)
BL	4	ripple blanking input (active LOW)
LE	5	latch enable input (active HIGH)
D0 to D3	7, 1, 2, 6	address (data) input
V _{SS}	8	ground supply voltage
Qa to Qg	13, 12, 11, 10, 9, 15, 14	segment output
V_{DD}	16	supply voltage

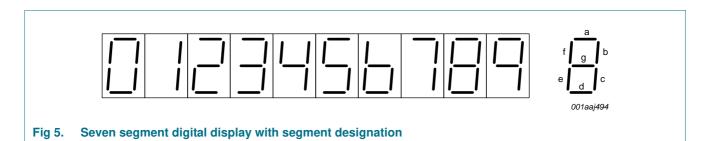
BCD to 7-segment latch/decoder/driver

6. Functional description

Table 3. Function table[1]

Input	S						Outpu	uts						Display
LE	BL	LT	D3	D2	D1	D0	Qa	Qb	Qc	Qd	Qe	Qf	Qg	
Χ	Χ	L	Χ	Χ	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	8
Χ	L	Н	Χ	Χ	Χ	Χ	L	L	L	L	L	L	L	blank
L	Н	Н	L	L	L	L	Н	Н	Н	Н	Н	Н	L	0
L	Н	Н	L	L	L	Н	L	Н	Н	L	L	L	L	1
L	Н	Н	L	L	Н	L	Н	Н	L	Н	Н	L	Н	2
L	Н	Н	L	L	Н	Н	Н	Н	Н	Н	L	L	Н	3
L	Н	Н	L	Н	L	L	L	Н	Н	L	L	Н	Н	4
L	Н	Н	L	Н	L	Н	Н	L	Н	Н	L	Н	Н	5
L	Н	Н	L	Н	Н	L	L	L	Н	Н	Н	Н	Н	6
L	Н	Н	L	Н	Н	Н	Н	Н	Н	L	L	L	L	7
L	Н	Н	Н	L	L	L	Н	Н	Н	Н	Н	Н	Н	8
L	Н	Н	Н	L	L	Н	Н	Н	Н	L	L	Н	Н	9
L	Н	Н	Н	L	Н	Χ	L	L	L	L	L	L	L	blank
L	Н	Н	Н	Н	Χ	Χ	L	L	L	L	L	L	L	blank
Н	Н	Н	Χ	Χ	Χ	Χ	N.C.	N.C.	N.C.	N.C.	N.C.	N.C.	N.C.	N.C.

 $[1] \quad H = HIGH \ voltage \ level; \ L = LOW \ voltage \ level; \ X = don't \ care; \ N.C. = no \ change.$



BCD to 7-segment latch/decoder/driver

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{DD} + 0.5 \text{ V}$	-	±10	mA
VI	input voltage		-0.5	$V_{DD} + 0.5$	V
l _{OK}	output clamping current	$V_O < -0.5 \; V$ or $V_O > V_{DD} + 0.5 \; V$	-	±10	mA
I _{I/O}	input/output current		-	±10	mA
I _{OH}	HIGH-level output current		<u>[1]</u> –25	-	mA
I_{DD}	supply current		-	50	mA
T _{stg}	storage temperature		-65	+150	°C
T _{amb}	ambient temperature		-40	+125	°C
P _{tot}	total power dissipation	T _{amb} = 125 °C			
		DIP16 package	[2] -	750	mW
		SO16 package	[3] _	500	mW
Р	power dissipation	per output	-	100	mW

^[1] A destructive high current mode may occur if V_I and V_O are not constrained to the range $V_{SS} \le V_I$ or $V_O \le V_{DD}$.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DD}	supply voltage		3	-	15	V
VI	input voltage		0	-	V_{DD}	V
T _{amb}	ambient temperature	in free air	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5 V$	-	-	3.75	μs/V
		V _{DD} = 10 V	-	-	0.5	μs/V
		V _{DD} = 15 V	-	-	0.08	μs/V

^[2] For DIP16 package: Ptot derates linearly with 12 mW/K above 70 °C.

^[3] For SO16 package: Ptot derates linearly with 8 mW/K above 70 °C.

BCD to 7-segment latch/decoder/driver

9. Static characteristics

Table 6. Static characteristics

 $V_{SS} = 0 \ V$; $V_I = V_{SS}$ or V_{DD} ; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T _{amb} =	–40 °C	T _{amb} =	+25 °C	T _{amb} =	+85 °C	T _{amb} =	+125 °C	Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level	$ I_0 < 1 \mu A$	5 V	3.5	-	3.5	-	3.5	-	3.5	-	٧
	input voltage		10 V	7.0	-	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level	$ I_O < 1 \mu A$	5 V	-	1.5	-	1.5	-	1.5	-	1.5	V
	input voltage		10 V	-	3.0	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	-	4.0	V
V _{OH}	HIGH-level output voltage	see <u>Table 7</u>	-	-	-	-	-	-	-	-	-	-
V _{OL}	LOW-level	$ I_0 < 1 \mu A$	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V
	output voltage		10 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V
I _{OH}	HIGH-level	$V_{O} = 2.5 \text{ V}$	5 V	-	-1.7	-	-1.4	-	-1.1	-	-1.1	mΑ
	output current	$V_{O} = 4.6 \text{ V}$	5 V	-	-0.64	-	-0.5	-	-0.36	-	-0.36	mΑ
		$V_{O} = 9.5 V$	10 V	-	-1.6	-	-1.3	-	-0.9	-	-0.9	mΑ
		$V_0 = 13.5 \text{ V}$	15 V	-	-4.2	-	-3.4	-	-2.4	-	-2.4	mΑ
I _{OL}	LOW-level	$V_0 = 0.4 \ V$	5 V	0.64	-	0.5	-	0.36	-	0.36	-	mΑ
	output current	$V_0 = 0.5 \text{ V}$	10 V	1.6	-	1.3	-	0.9	-	0.9	-	mΑ
		$V_0 = 1.5 \text{ V}$	15 V	4.2	-	3.4	-	2.4	-	2.4	-	mΑ
II	input leakage current		15 V	-	±0.1	-	±0.1	-	±1.0	-	±1.0	μА
I _{DD}	supply current	$I_O = 0 A$	5 V	-	5	-	5	-	150	-	150	μΑ
			10 V	-	10	-	10	-	300	-	300	μΑ
			15 V	-	20	-	20	-	600	-	600	μΑ
C _I	input capacitance		-	-	-	-	7.5	-	-	-	-	pF

BCD to 7-segment latch/decoder/driver

Table 7. Static characteristics for V_{OH} $V_{SS} = 0 \ V$.

Symbol	Parameter	I _{OH}	V_{DD}	T _{amb} = -40 °C	T _{amb} =	+25 °C	T _{amb} = +85 °C	T _{amb} = +125 °C	Unit
		mA	٧	Min	Min	Тур	Min	Min	
V_{OH}	HIGH-level	0	5 V	4.10	4.10	4.40	4.10	4.10	٧
V _{OH} HI	output voltage		10 V	9.10	9.10	9.90	9.10	9.10	V
			15 V	14.10	14.10	14.40	14.10	14.10	V
		Max V Min Min Min IGH-level autput voltage	4.30	-	-	V			
			10 V	-	-	9.30	-	-	٧
			15 V	-	-	14.30	-	-	٧
		10	5 V	3.60	3.60	4.25	3.30	3.20	٧
			10 V	8.75	8.75	9.25	8.45	8.35	٧
			15 V	13.75	13.75	14.30	13.45	13.35	٧
		15	5 V	-	-	4.20	-	-	٧
			10 V	-	-	9.20	-	-	٧
			15 V	-	-	14.20	-	-	٧
		20	5 V	2.80	2.80	4.20	2.50	2.30	٧
			10 V	8.10	8.10	9.20	7.80	7.60	٧
			15 V	13.10	13.10	14.20	12.80	12.60	V
		25	5 V	-	-	4.15	-	-	V
			10 V	-	-	9.20	-	-	V
			15 V	-	-	14.20	-	-	V

10. Dynamic characteristics

Table 8. Dynamic characteristics

 $V_{SS} = 0 \ V; T_{amb} = 25 \ ^{\circ}C;$ for test circuit see <u>Figure 8</u>.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula[1]	Min	Тур	Max	Unit
t _{PHL}	HIGH to LOW	$Dn \rightarrow Qn;$	5 V	128 ns + $(0.55 \text{ ns/pF})C_L$	-	155	310	ns
	propagation delay	see Figure 6	10 V	49 ns + (0.23 ns/pF)C _L	-	60	120	ns
			15 V	$32 \text{ ns} + (0.16 \text{ ns/pF})C_L$	-	40	80	ns
		$LE \rightarrow Qn;$	5 V	133 ns + $(0.55 \text{ ns/pF})C_L$	-	160	320	ns
		see Figure 6	10 V	49 ns + $(0.23 \text{ ns/pF})C_L$	-	60	120	ns
			15 V	$37 \text{ ns} + (0.16 \text{ ns/pF})C_L$	-	45	90	ns
		$\overline{BL} \to Qn;$	5 V	93 ns + $(0.55 \text{ ns/pF})C_L$	-	120	240	ns
		see <u>Figure 6</u>	10 V	$39 \text{ ns} + (0.23 \text{ ns/pF})C_L$	-	50	100	ns
			15 V	27 ns + $(0.16 \text{ ns/pF})C_L$	-	35	70	ns
		$\overline{\text{LT}} \rightarrow \text{Qn};$	5 V	52 ns + $(0.55 \text{ ns/pF})C_L$	-	80	160	ns
		see <u>Figure 6</u>	10 V	19 ns + (0.23 ns/pF)C _L	-	30	60	ns
			15 V	12 ns + (0.16 ns/pF)C _L	-	20	40	ns

BCD to 7-segment latch/decoder/driver

Table 8. Dynamic characteristics ...continued $V_{SS} = 0 \ V; T_{amb} = 25 \ ^{\circ}C;$ for test circuit see <u>Figure 8</u>.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula[1]	Min	Тур	Max	Unit
t _{PLH}	LOW to HIGH	$Dn \rightarrow Qn;$	5 V	108 ns + $(0.55 \text{ ns/pF})C_L$	-	135	270	ns
	propagation delay	see Figure 6	10 V	44 ns + (0.23 ns/pF)C _L	-	55	110	ns
			15 V	32 ns + $(0.16 \text{ ns/pF})C_L$	-	40	80	ns
		$LE \rightarrow Qn;$	5 V	133 ns + (0.55 ns/pF)C _L	-	160	320	ns
		see Figure 6	10 V	59 ns + $(0.23 \text{ ns/pF})C_L$	-	70	270 110 80	ns
			15 V	42 ns + $(0.16 \text{ ns/pF})C_L$	-	50		ns
		$\overline{BL} \to Qn;$	5 V	78 ns + $(0.55 \text{ ns/pF})C_L$	-	105	210	ns
		see Figure 6	10 V	29 ns + $(0.23 \text{ ns/pF})C_L$	-	40	80	ns
			15 V	22 ns + $(0.16 \text{ ns/pF})C_L$	-	30	60	ns
		$\overline{\text{LT}} \rightarrow \text{Qn};$	5 V	33 ns + $(0.55 \text{ ns/pF})C_L$	-	60	120	ns
		see Figure 6	10 V	19 ns + $(0.23 \text{ ns/pF})C_L$	-	30	60	ns
			15 V	17 ns + $(0.16 \text{ ns/pF})C_L$	-	25	50	ns
t _{THL}	HIGH to LOW output	see Figure 6	5 V	10 ns + $(1.00 \text{ ns/pF})C_L$	-	60	120	ns
	transition time		10 V	9 ns + $(0.42 \text{ ns/pF})C_L$	-	30	60	ns
			15 V	6 ns + $(0.28 \text{ ns/pF})C_L$	-	20	40	ns
t _{TLH}	LOW to HIGH output	see Figure 6	5 V	20 ns + $(1.00 \text{ ns/pF})C_L$	-	25	50	ns
	transition time		10 V	13 ns + $(0.06 \text{ ns/pF})C_L$	-	16	32	ns
			15 V	10 ns + $(0.06 \text{ ns/pF})C_L$	-	13	26	ns
t _{su}	set-up time	$Dn \rightarrow LE;$	5 V		50	25	-	ns
		see Figure 7	10 V		25	12	-	ns
			15 V		20	9	-	ns
t _h	hold time	$Dn \rightarrow LE;$	5 V		60	30	-	ns
		see Figure 7	10 V		30	15	-	ns
			15 V		25	12	-	ns
t _W	pulse width	LE input LOW;	5 V		80	40	-	ns
		minimum width; see Figure 7	10 V		40	20	320 140 100 15 210 80 60 120 60 60 120 60 40 50 32 60 7 7 8 8 7 8 8 8 8 8 8 8 8 8 8 8 8 8	ns
		see <u>rigule /</u>	15 V		35	17	-	ns

^[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).

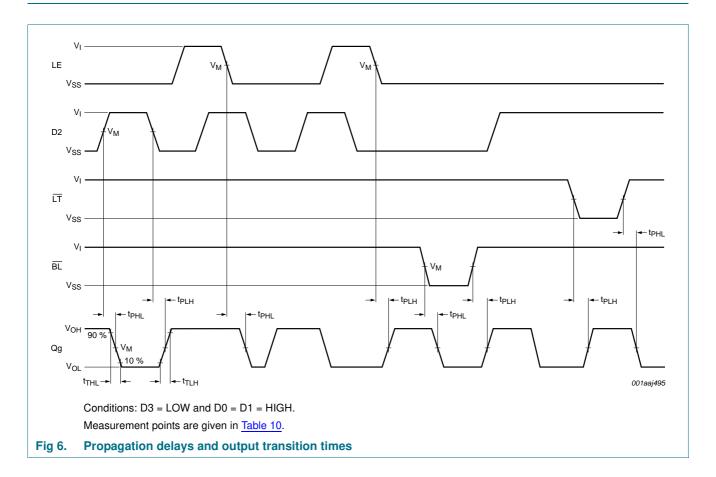
Table 9. Dynamic power dissipation P_D

 P_D can be calculated from the formulas shown. $V_{SS} = 0 \ V$; $t_r = t_f \le 20 \ ns$; $T_{amb} = 25 \ ^{\circ}C$.

Symbol	Parameter	V_{DD}	Typical formula for P _D (μW)	where:
P_D	dynamic power	5 V	$P_D = 1000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}{}^2$	f_i = input frequency in MHz;
	dissipation	10 V	$P_D = 4000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	fo = output frequency in MHz;
		15 V	$P_D = 10000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	C_L = output load capacitance in pF;
				V_{DD} = supply voltage in V;
				$\Sigma(f_0\times C_L)=$ sum of the outputs.

BCD to 7-segment latch/decoder/driver

11. Waveforms



BCD to 7-segment latch/decoder/driver

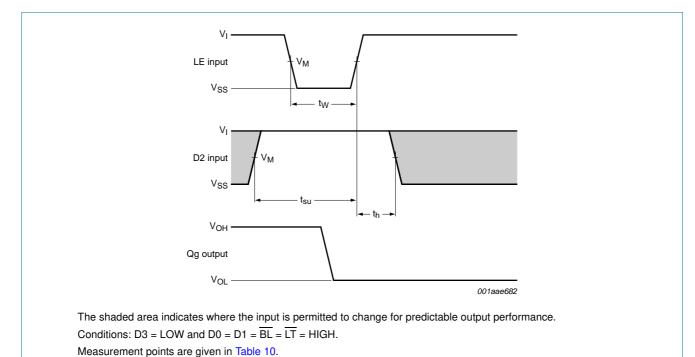
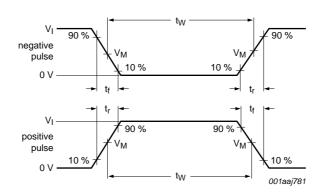
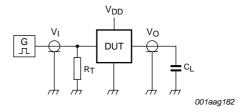


Fig 7. Waveforms showing minimum LE pulse width, set-up, and hold time for Dn to LE

BCD to 7-segment latch/decoder/driver



a. Input waveforms



b. Test circuit

Test data is given in <u>Table 10</u>.

Definitions for test circuit:

DUT = Device Under Test.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

Fig 8. Test circuit for measuring switching times

Table 10. Measurement points and test data

Supply voltage	Input			Load
	V _I	V _M	t _r , t _f	C _L
5 V to 15 V	V_{DD}	0.5V _I	≤ 20 ns	50 pF

BCD to 7-segment latch/decoder/driver

12. Application information

- · Driving LED displays
- · Driving incandescent displays
- · Driving fluorescent displays
- Driving LCD displays
- · Driving gas discharge displays

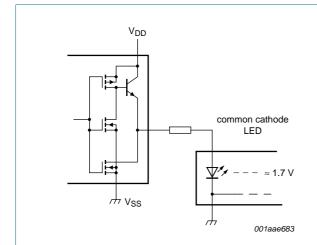


Fig 9. Connection to common cathode LED display readout

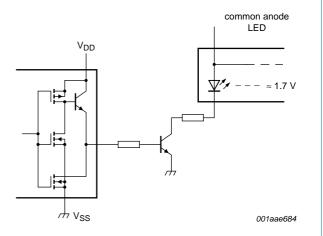
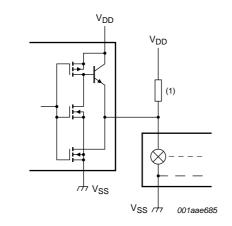


Fig 10. Connection to common anode LED display readout



(1) A filament pre-warm resistor is recommended to reduce filament thermal shock and increase the effective cold resistance of the filament.

Fig 11. Connection to incandescent display readout

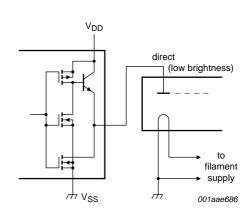
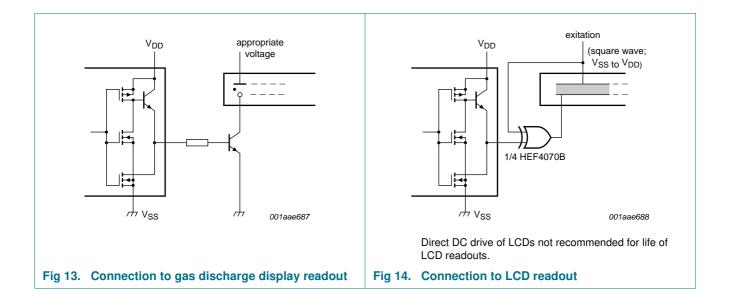


Fig 12. Connection to fluorescent display readout

BCD to 7-segment latch/decoder/driver

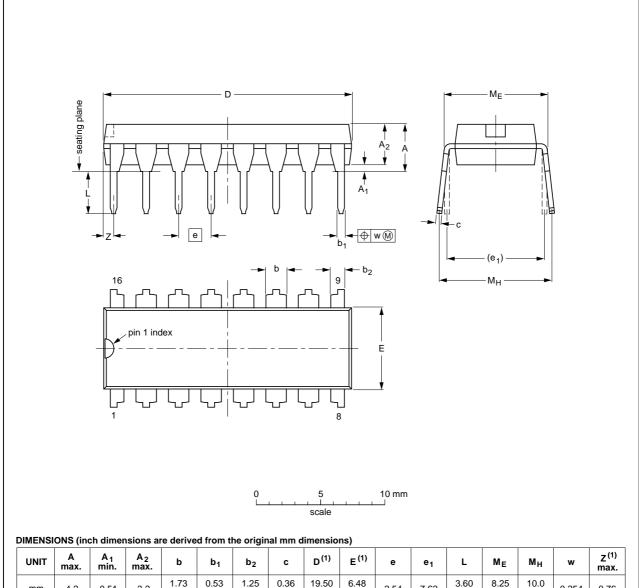


BCD to 7-segment latch/decoder/driver

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE
	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT38-4						95-01-14 03-02-13

Fig 15. Package outline SOT38-4 (DIP16)

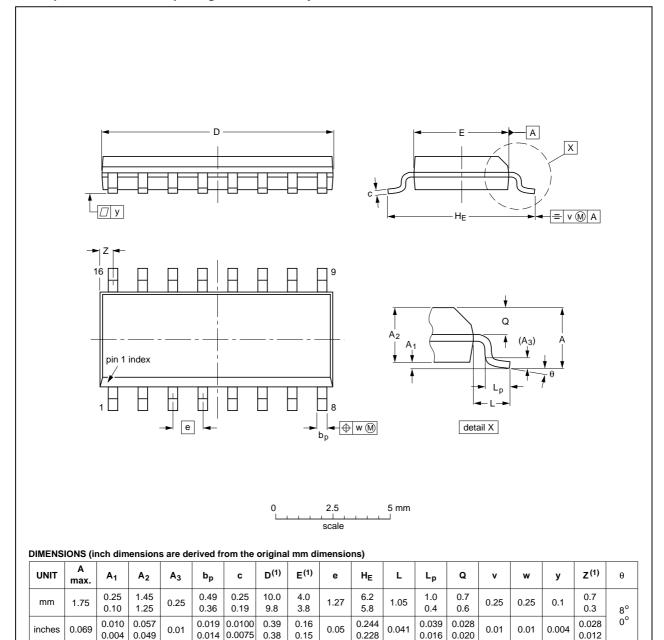
HEF4511E

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SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE
	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT109-1	076E07	MS-012				99-12-27 03-02-19

Fig 16. Package outline SOT109-1 (SO16)

HEF4511B

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HEF4511B NXP Semiconductors

BCD to 7-segment latch/decoder/driver

14. Revision history

Table 11. Revision history

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4511B v.7	20111111	Product data sheet	-	HEF4511B v.6
Modifications:	 Section App 	olications removed		
	 <u>Table 6</u>: I_{OH} 	_I minimum values changed t	o maximum	
HEF4511B v.6	20091207	Product data sheet	-	HEF4511B v.5
HEF4511B v.5	20090813	Product data sheet	-	HEF4511B v.4
HEF4511B v.4	20090305	Product data sheet	-	HEF4511B_CNV v.3
HEF4511B_CNV v.3	19950101	Product specification	-	HEF4511B_CNV v.2
HEF4511B_CNV v.2	19950101	Product specification	-	-

BCD to 7-segment latch/decoder/driver

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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BCD to 7-segment latch/decoder/driver

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16. Contact information

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HEF4511B NXP Semiconductors

BCD to 7-segment latch/decoder/driver

17. Contents

1	General description	. 1
2	Features and benefits	. 1
3	Ordering information	. 1
4	Functional diagram	. 2
5	Pinning information	. 4
5.1	Pinning	. 4
5.2	Pin description	. 4
6	Functional description	. 5
7	Limiting values	. 6
8	Recommended operating conditions	. 6
9	Static characteristics	. 7
10	Dynamic characteristics	. 8
11	Waveforms	10
12	Application information	13
13	Package outline	15
14	Revision history	17
15	Legal information	18
15.1	Data sheet status	18
15.2	Definitions	
15.3	Disclaimers	
15.4	Trademarks	19
16	Contact information	19
17	Contents	20

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